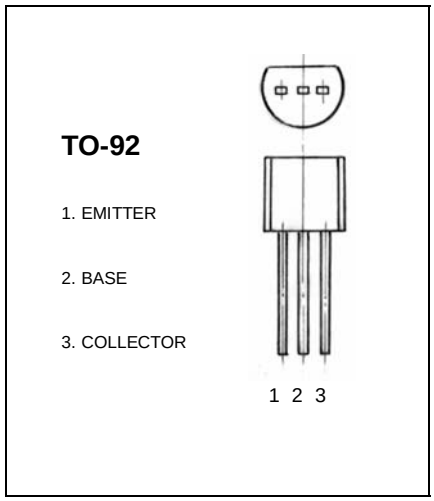
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

MPS2907 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 0.625 W (Tamb=25℃)

Collector current

I_{CM}: -0.6 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -10μA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA , I_B=0	-40			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -50V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -35V, I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3 V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V, I_C= -150mA	100		300	
	$h_{FE(2)}$	V_{CE}=-10V, I_C= -1mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-50 mA			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -500mA, I_B=-50 mA			-2	V
Transition frequency	f_T	V_{CE}=-20 V, I_C= -50mA f = 100MHz	200			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	100-200	200-300